

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2N3375** is Designed for Class A,B,C Amplifier,Oscillator and Driver Applications Covering the VHF-UHF Region.

FEATURES INCLUDE:

- Isolated Package

MAXIMUM RATINGS

I_C	1.5 A
V_{CE}	40 V
P_{DISS}	11.6 W @ T _C = 25 °C
T_J	-65°C to +200 °C
T_{STG}	-65°C to +200 °C
θ_{JC}	15 °C/W

PACKAGE STYLE TO-60(ISOLATED)

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.090/2,29	.110/2,79
B	.185/4,70	.215/5,46
C	.420/10,67	.440/11,18
D	.030/0,76	.046/1,17
E	.320/8,13	.360/9,14
F	.090/2,29	.135/3,43
G	.215/5,46	.320/8,13
H		.480/12,19
I	.420/10,67	.455/11,56

1 = EMITTER 2 = BASE
3 = COLLECTOR

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA	40			V
BV_{CEX}	V _{BE} = -1.5 V I _C = 100 mA	65			V
BV_{CBO}	I _C = 500 μA	65			V
I_{CEO}	V _{CE} = 30 V			100	μA
I_{EBO}	V _{EB} = 4.0 V			100	μA
h_{FE}	V _{CE} = 5.0 V I _C = 250 mA	10			---
V_{CE(SAT)}	I _C = 500 mA I _B = 100 mA			1.0	V
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			10	pF
f_t	V _{CE} = 28 V I _C = 150 mA f = 100 MHz		500		MHz
P_{out}	V _{CE} = 28 V P _{in} = 1.0 W f = 400 MHz	3.0			W
G_p		4.8			dB
η		40			%